

# **High Performance Bipolar NPN RF Transistor**

- High transducer gain of typ. 14 dB @ 25 mA,6 GHz
- Low minimum noise figure of typ. 0.85 dB @ 6GHz
- High output compression of typ. 11 dBm @ 25 mA
- Pb-free (RoHS compliant) package
- For a wide range of non-automotive applications
  - 2nd and 3rd LNA stage and mixer stage in LNB
  - 5.8 GHz analog/digital cordless phone
  - Satellite radio SDARS
  - WLAN, WiMAX, UWB



# 3 2 2

ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking		Р	in Con	figurati	on		Package
BF888	RYs	1=B	2=E	3=C	4=E	-	-	SOT343

**Maximum Ratings** at  $T_A$  = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$		V
<i>T</i> <sub>A</sub> = 25 °C		4.0	
<i>T</i> <sub>A</sub> = − 55 °C		3.5	
Collector-emitter voltage	$V_{CES}$	13	
Collector-base voltage	$V_{CBO}$	13	
Emitter-base voltage	$V_{EBO}$	1.2	
Collector current	I <sub>C</sub>	30	mA
Base current	I <sub>B</sub>	3	
Total power dissipation <sup>1)</sup>	P <sub>tot</sub>	160	mW
<i>T</i> <sub>S</sub> ≤ 89 °C			
Junction temperature	TJ	150	°C
Ambient temperature	T <sub>A</sub>	-55 150	
Storage temperature	$T_{\mathrm{Stg}}$	-55 150	

 $<sup>^{1}</sup>T_{\mathrm{S}}$  is measured on the emitter lead at the soldering point to the pcb

### **Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	R <sub>thJS</sub>	≤ 380	K/W



# **Electrical Characteristics** at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics				•	•
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	4	4.7	-	V
$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$					
Collector-emitter cutoff current	I <sub>CES</sub>	-	1	-	nA
$V_{CE} = 5 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I <sub>CBO</sub>	-	1	-	
$V_{\rm CB} = 5  \text{V},  I_{\rm E} = 0$					
Emitter-base cutoff current	I <sub>EBO</sub>	-	10	-	
$V_{\rm EB} = 0.5  \text{V}, I_{\rm C} = 0$					
DC current gain	h <sub>FE</sub>	-	250	_	-
$I_{\rm C}$ = 25 V, $V_{\rm CE}$ = 3 V, pulse measured					

 $<sup>^{1}\</sup>mbox{For calculation of}\,R_{\mbox{\scriptsize thJA}}$  please refer to Application Note Thermal Resistance



**Electrical Characteristics** at  $T_A = 25$ °C, unless otherwise specified

Parameter Parameter $I_A = 25^{\circ}$ C, unless	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling	3)				
Transition frequency	$f_{T}$	-	47	-	GHz
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $f$ = 2 GHz					
Collector-base capacitance	C <sub>cb</sub>	-	0.08	-	pF
$V_{\text{CB}}$ = 3 V, f=1 MHz, $V_{\text{BE}}$ = 0, emitter grounded					
Collector emitter capacitance	C <sub>ce</sub>	_	0.35	-	
$V_{CE}$ = 3 V, $f$ = 1 MHz, $V_{BE}$ = 0, base grounded					
Emitter-base capacitance	C <sub>eb</sub>	-	0.45	-	
$V_{\text{EB}}$ = 0.5 V, $f$ =1 MHz, $V_{\text{CB}}$ =0, collector grounded					
Noise figure	F				dB
$I_{C}$ = 8 mA, $V_{CE}$ = 3 V, $f$ = 1.8 GHz, $Z_{S}$ = $Z_{Sopt}$		_	0.5	-	
$I_{C}$ = 8 mA, $V_{CE}$ = 3 V, $f$ = 6 GHz, $Z_{S}$ = $Z_{Sopt}$		-	0.85	-	
Power gain	G <sub>ms</sub>	-	27	-	dB
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,					
f = 1.8 GHz					
Power gain, maximum available <sup>1)</sup>	G <sub>ma</sub>	-	17	-	dB
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,					
f = 6 GHz					
Transducer gain	S <sub>21e</sub>   <sup>2</sup>				dB
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,					
f = 1.8 GHz		_	24.5	-	
f = 6 GHz		-	14	-	
Third order intercept point at output <sup>2)</sup>	IP <sub>3</sub>	-	25	-	dBm
$V_{CE}$ = 3 V, $I_{C}$ = 25 mA, $f$ = 1.8 GHz,					
$Z_{\rm S} = Z_{\rm L} = 50 \ \Omega$					
1dB Compression point	P <sub>-1dB</sub>	-	11	-	
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,					
f = 1.8 GHz					

 $<sup>{}^{1}</sup>G_{\text{ma}} = |S_{21e} / S_{12e}| (k-(k^{2}-1)^{1/2})$ 

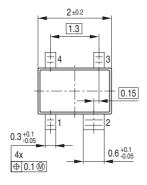
<sup>&</sup>lt;sup>2</sup>IP3 value depends on termination of all intermodulation frequency components.

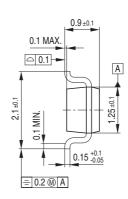
Termination used for this measurement is 50  $\Omega$  from 0.1 MHz to 6 GHz



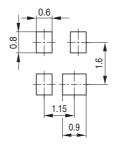
# Package Outline



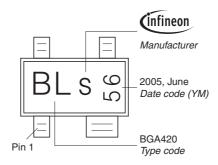




# Foot Print

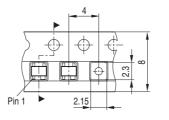


# Marking Layout (Example)



# Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel







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